

Claims

[c1] What is claimed is:

1. A ceramic susceptor having a side for retaining an object being processed, the susceptor comprising:
a resistive-heating-element circuit formed on one surface selected from a surface on other than said retaining side, and a susceptor internal surface; and
a lead circuit for supplying electricity to the resistive heating element, formed on a surface different from the surface on which said resistive heating element is formed.

[c2] 2. A susceptor as set forth in claim 1, wherein said resistive-heating-element circuit is patterned in approximately concentric circular forms.

[c3] 3. A susceptor as set forth in claim 1, wherein said lead circuit three-dimensionally intersects said resistive-heating-element circuit.

[c4] 4. A susceptor as set forth in claim 1, wherein said resistive-heating-element circuit is patterned in a plurality of discrete zones.

- [c5] 5. A susceptor as set forth in claim 1, wherein the temperature uniformity in said side for retaining an object being processed is within $\pm 1.0\%$.
- [c6] 6. A susceptor as set forth in claim 1, wherein the resistance of said lead circuit is smaller than the resistance of said resistive-heating-element circuit.
- [c7] 7. A susceptor as set forth in claim 1, further comprising electrodes for supplying electric power from without, said electrodes formed proximate to roughly the center of the ceramic susceptor and connected to said lead circuit.
- [c8] 8. A susceptor as set forth in claim 1, wherein the susceptor thickness is 5 mm or more.
- [c9] 9. A susceptor as set forth in claim 1, wherein the chief component of the susceptor ceramic is one selected from aluminum oxide, silicon nitride and aluminum nitride.
- [c10] 10. A susceptor as set forth in claim 9, wherein the chief component of said ceramic is aluminum nitride.
- [c11] 11. A susceptor as set forth in claim 10, wherein an yttrium compound is added as a sintering aid into the ceramic.

- [c12] 12. A susceptor as set forth in claim 11, wherein the amount of the yttrium compound added is 0.01 weight % or more, and 5.0 weight % or less, in yttrium oxide (Y_2O_3) equivalent.
- [c13] 13. A semiconductor manufacturing apparatus in which the ceramic susceptor recited in claim 1 is installed.
- [c14] 14. A liquid-crystal manufacturing apparatus in which the ceramic susceptor recited in claim 1 is installed.